

18N65

Power MOSFET

18A, 650V N-CHANNEL
POWER MOSFET

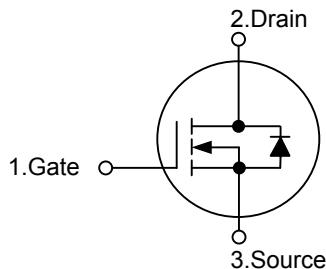
■ DESCRIPTION

The UTC **18N65** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * $R_{DS(ON)} \leq 0.5\Omega$ @ $V_{GS}=10V$, $I_D=9.0A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL



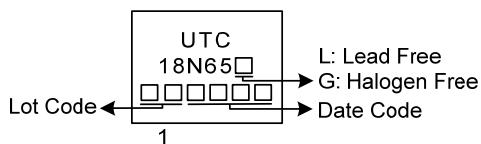
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
18N65L-T3P-T	18N65G-T3P-T	TO-3P	G	D	S	Tube
18N65L-T3N-T	18N65G-T3N-T	TO-3PN	G	D	S	Tube
18N65L-T47-T	18N65G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) T: Tube (2) T3P: TO-3P, T3N: TO-3PN, T47: TO-247 (3) G: Halogen Free and Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	650	V
Gate-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current		I _D	18	A
Pulsed Drain Current		I _{DM}	45	A
Avalanche Energy	Single Pulsed	E _{AS}	938 (Note 2)	mJ
Peak Diode Recovery dv/dt		dv/dt	10	V/ns
Power Dissipation	TO-3P/TO-3PN	P _D	390	W
	TO-247		357	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. L=10mH, I_{AS}=13.7A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-3P/TO-3PN	θ _{JA}	30	°C/W
	TO-247		40	°C/W
Junction to Case	TO-3P/TO-3PN	θ _{JC}	0.32	°C/W
	TO-247		0.35	°C/W

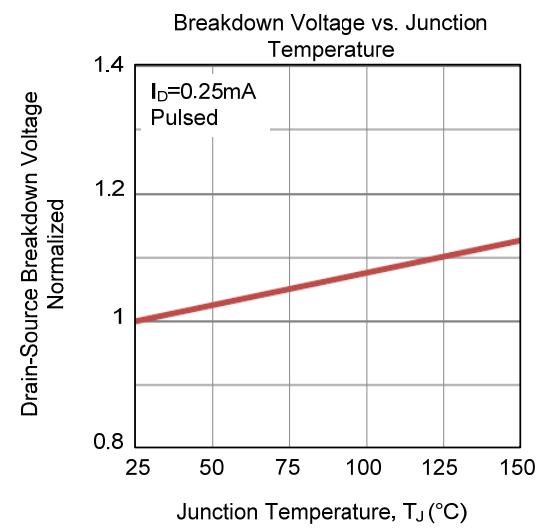
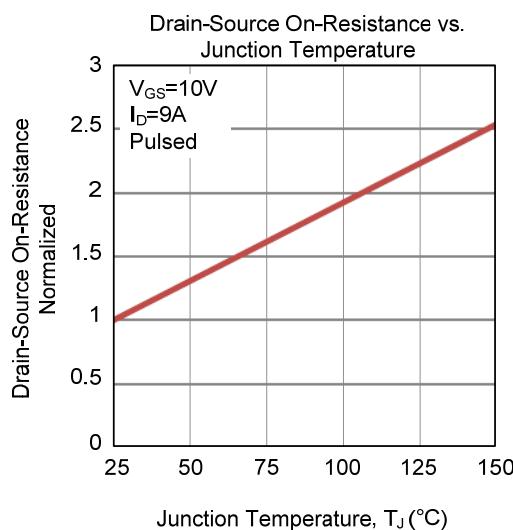
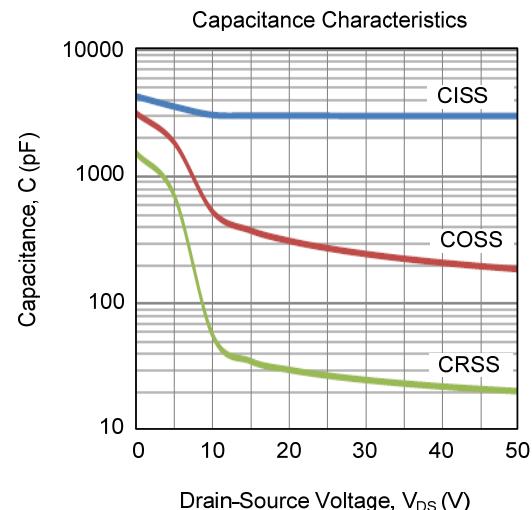
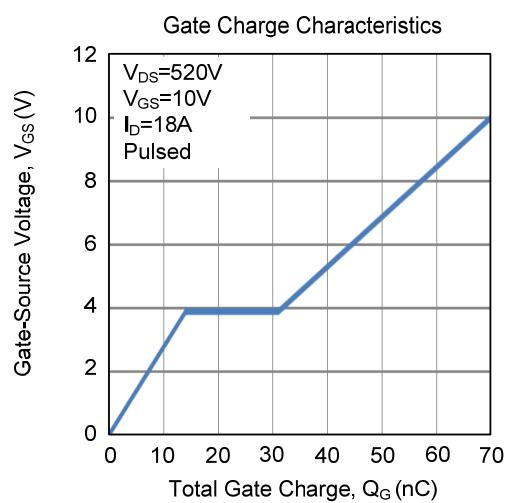
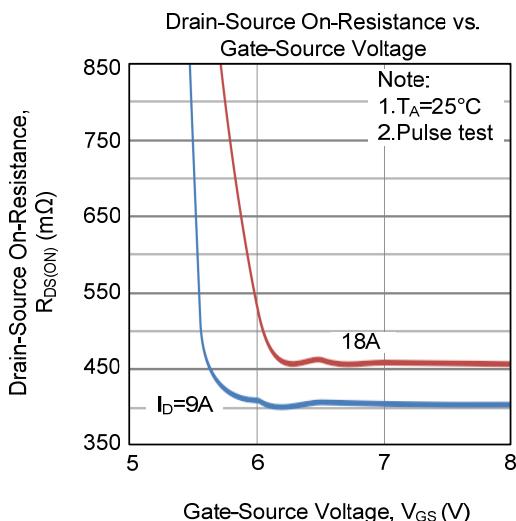
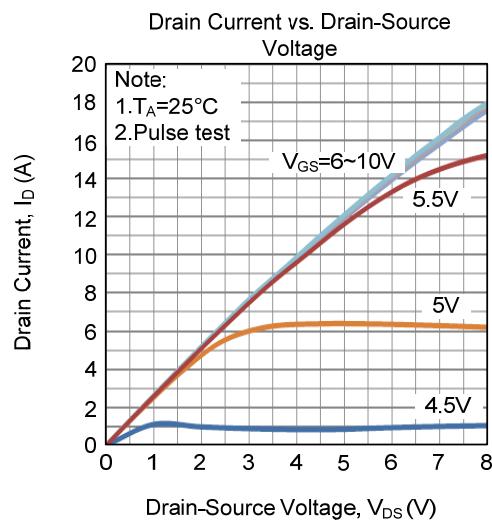
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650			V
Drain-Source Leakage Current	$I_{\text{DS}(\text{SS})}$	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$			25	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 30\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=9.0\text{A}$ (Note)			0.5	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		3020		pF
Output Capacitance	C_{OSS}			273		pF
Reverse Transfer Capacitance	C_{RSS}			27		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{\text{DS}}=520\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=18\text{A}$ $I_{\text{G}}=1\text{mA}$ (Note 1,2)		70		nC
Gate Source Charge	Q_{GS}			14		nC
Gate Drain Charge	Q_{GD}			17		nC
Turn-ON Delay Time	$t_{\text{D(ON)}}$	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=100\text{V},$ $I_{\text{D}}=18\text{A}, R_{\text{G}}=25\Omega$ (External) (Note 1,2)		46		ns
Turn-ON Rise Time	t_R			27		ns
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			206		ns
Turn-OFF Fall-Time	t_F			87		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S	$V_{\text{GS}}=0\text{V}$			18	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	Repetitive			54	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_F=I_S, V_{\text{GS}}=0\text{V}$ (Note)			1.5	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}}=0\text{V}, dI_F/dt=100\text{A}/\mu\text{s},$ $I_S=18\text{A}, V_R=400\text{V}$		536		ns
Reverse Recovery Charge	Q_{rr}			10		μC

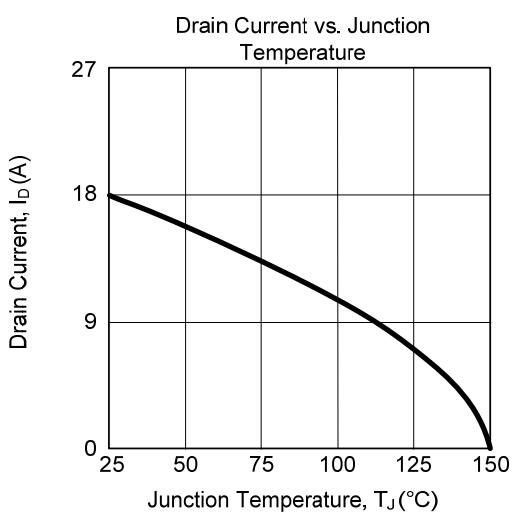
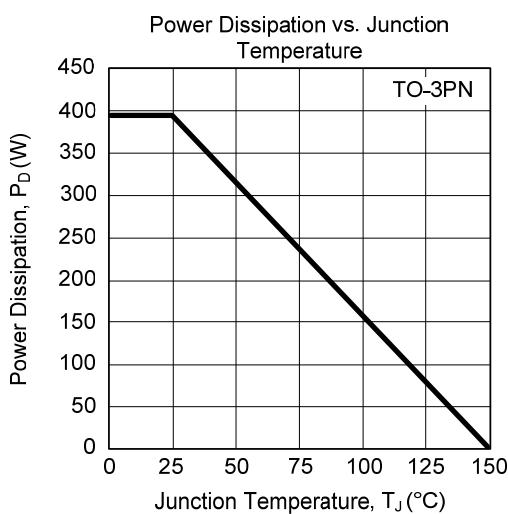
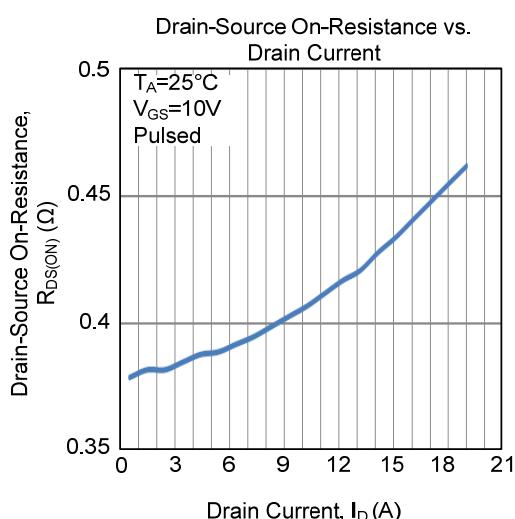
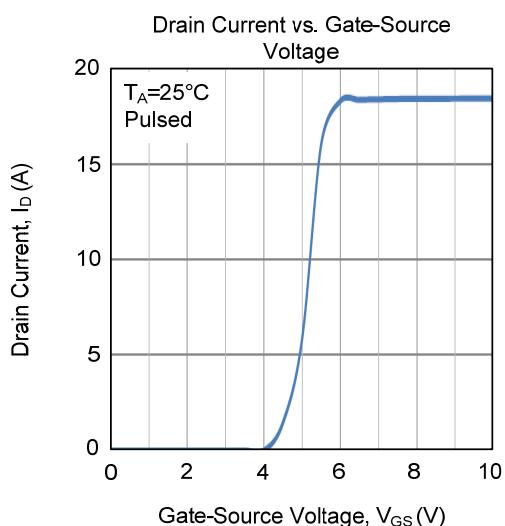
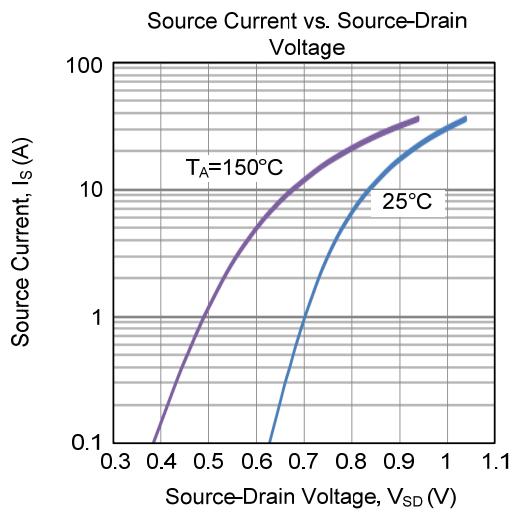
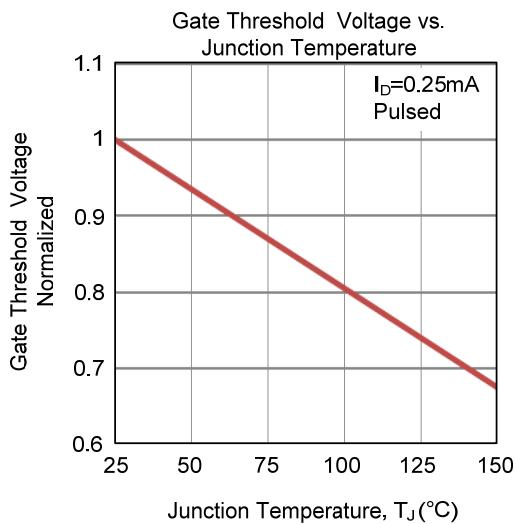
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

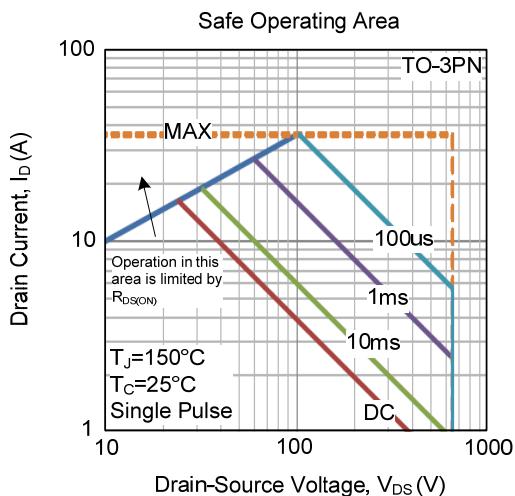
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



- TYPICAL CHARACTERISTICS (Cont.)



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